

BF370 TRANSISTOR (NPN)

FEATURES

Power dissipation

$$P_{CM}: 0.5 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

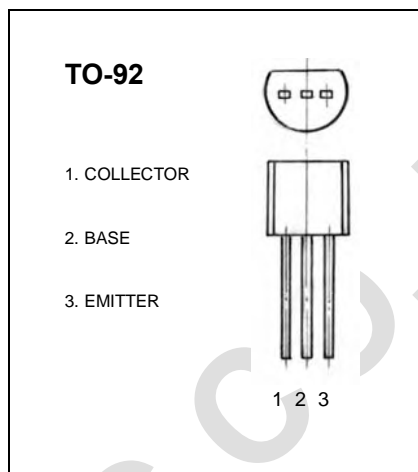
$$I_{CM}: 0.1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: 40 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	15			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	4.5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 20\text{V}, I_E = 0$			0.4	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 2\text{V}, I_C = 0$			0.1	μA
DC current gain	h_{FE}	$V_{CE} = 1\text{V}, I_C = 10\text{mA}$	40		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 15\text{mA}, I_B = 1.5 \text{ mA}$			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 15\text{mA}, I_B = 1.5 \text{ mA}$			1.2	V
Transition frequency	f_T	$V_{CE} = 10\text{V}, I_C = 10\text{mA}$ $f = 100\text{MHz}$	500			MHz